

Switching (−30V, −5.0A)

RSS050P03

●Features

- 1) Low On-resistance.
- 2) Built-in G-S Protection Diode.
- 3) Small and Surface Mount Package (SOP8).

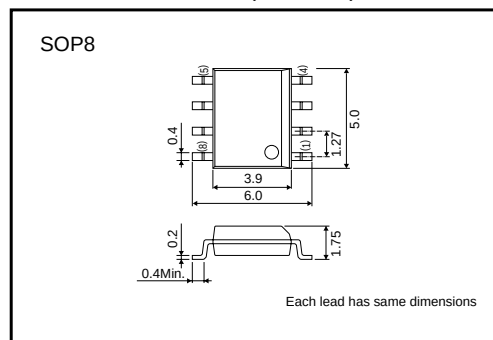
●Application

Power switching, DC / DC converter.

●Structure

Silicon P-channel
MOS FET

●External dimensions (Unit : mm)



●Packaging specifications

Type	Package	Taping
	Code	TB
	Basic ordering unit (pieces)	2500
RSS050P03		○

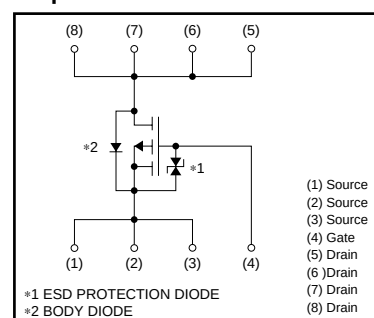
●Absolute maximum ratings (Ta=25°C)

Parameter	Symbol	Limits	Unit
Drain-source voltage	V_{DS}	−30	V
Gate-source voltage	V_{GS}	±20	V
Drain current	Continuous	I_D	±5.0 A
	Pulsed	I_{DP}	±20 A *1
Source current (Body diode)	Continuous	I_S	−1.6 A
	Pulsed	I_{SP}	−20 A *1
Total power dissipation	P_D	2.0	W *2
Channel temperature	T_{ch}	150	°C
Range of Storage temperature	T_{stg}	−55 to +150	°C

*1 $P_W \leq 10 \mu s$, Duty cycle $\leq 1\%$

*2 Mounted on a ceramic board

●Equivalent circuit



●Thermal resistance (Ta=25°C)

Parameter	Symbol	Limits	Unit
Channel to ambient	$R_{th (ch-a)}$	62.5	°C / W *

* Mounted on a ceramic board.

Transistors

●Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Gate-source leakage	I_{GSS}	—	—	± 10	μA	$V_{GS}=\pm 20V$, $V_{DS}=0V$
Drain-source breakdown voltage	$V_{(BR) DSS}$	-30	—	—	V	$I_D = -1mA$, $V_{GS}=0V$
Zero gate voltage drain current	I_{DSS}	—	—	-1	μA	$V_{DS} = -30V$, $V_{GS}=0V$
Gate threshold voltage	$V_{GS(th)}$	-1.0	—	-2.5	V	$V_{DS} = -10V$, $I_D = -1mA$
Static drain-source on-state resistance	$R_{DS(on)}$ *	—	30	42	$m\Omega$	$I_D = -5.0A$, $V_{GS} = -10V$
		—	47	65	$m\Omega$	$I_D = -2.5A$, $V_{GS} = -4.5V$
		—	55	77	$m\Omega$	$I_D = -2.5A$, $V_{GS} = -4.0V$
Forward transfer admittance	$ Y_{fs} $ *	5.0	—	—	S	$V_{DS} = -10V$, $I_D = -2.5A$
Input capacitance	C_{iss}	—	1200	—	pF	$V_{DS} = -10V$
Output capacitance	C_{oss}	—	250	—	pF	$V_{GS}=0V$
Reverse transfer capacitance	C_{rss}	—	180	—	pF	$f=1MHz$
Turn-on delay time	$t_{d(on)}$ *	—	12	—	ns	$I_D = -2.5A$
Rise time	t_r *	—	25	—	ns	$V_{DD} = -15V$
Turn-off delay time	$t_{d(off)}$ *	—	70	—	ns	$V_{GS} = -10V$
Fall time	t_f *	—	35	—	ns	$R_L=6\Omega$
Total gate charge	Q_g	—	13	—	nC	$V_{DD} = -15V$
Gate-source charge	Q_{gs}	—	2.8	—	nC	$V_{GS} = -5V$
Gate-drain charge	Q_{gd}	—	5.0	—	nC	$I_D = -5.0A$

*Pulsed

Body diode characteristics (source-drain characteristics)

Forward voltage	V_{SD}	—	—	-1.2	V	$I_S = -1.6A$, $V_{GS}=0V$
-----------------	----------	---	---	------	---	-----------------------------

Transistors

●Electrical characteristic curves

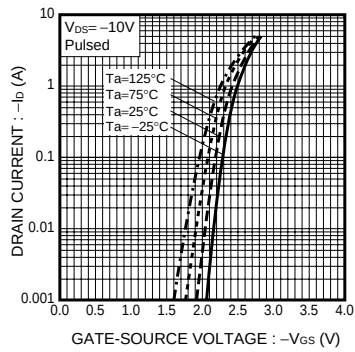


Fig.1 Typical Transfer Characteristics

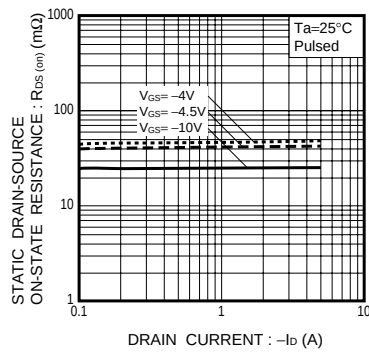


Fig.2 Static Drain-Source On-State Resistance vs. Drain Current

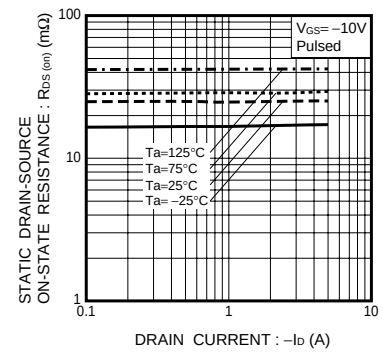


Fig.3 Static Drain-Source On-State Resistance vs. Drain Current

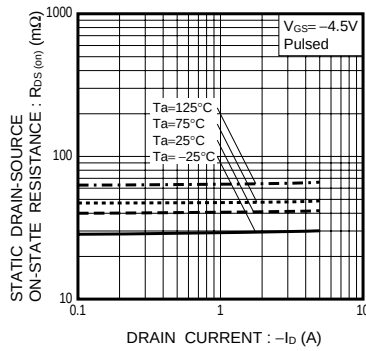


Fig.4 Static Drain-Source On-State Resistance vs. Drain Current

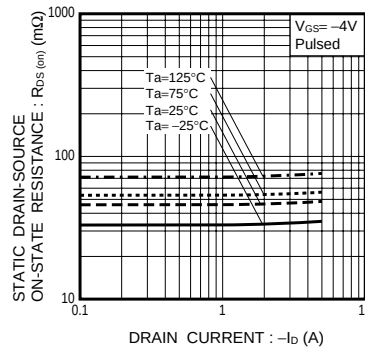


Fig.5 Static Drain-Source On-State Resistance vs. Drain Current

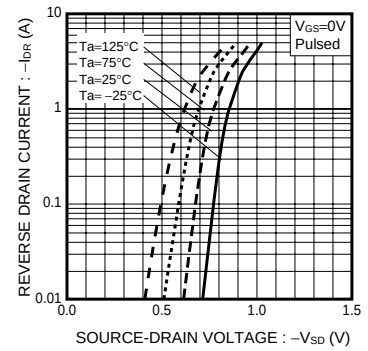


Fig.6 Reverse Drain Current Source-Drain Current

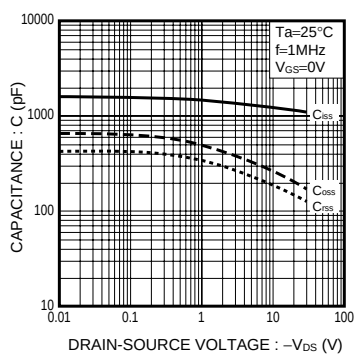


Fig.7 Typical Capacitance vs. Drain-Source Voltage

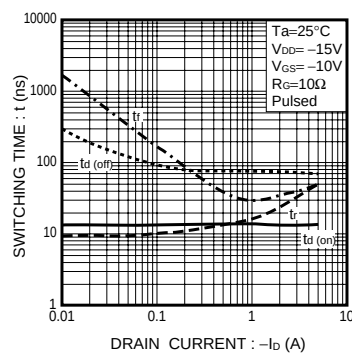


Fig.8 Switching Characteristics

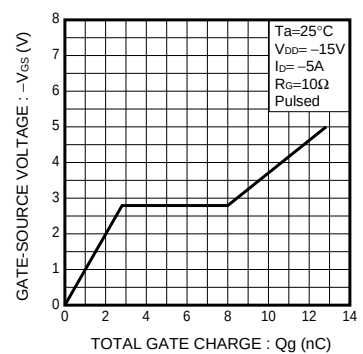


Fig.9 Dynamic Input Characteristics

Transistors

●Measurement circuits

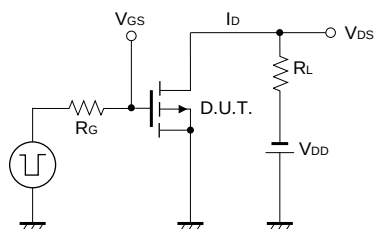


Fig.10 Switching Time Test Circuit

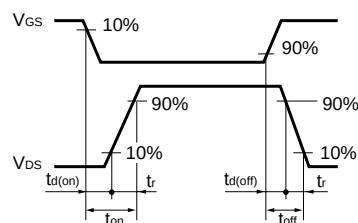


Fig.11 Switching Time Waveforms

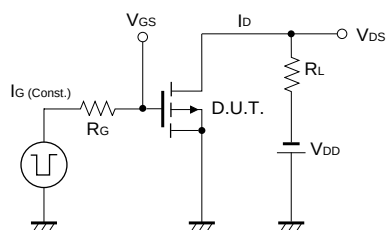


Fig.12 Gate Charge Test Circuit

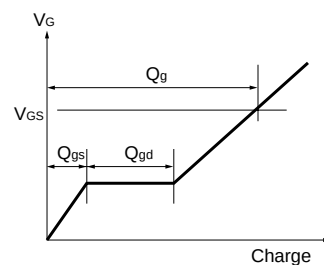


Fig.13 Gate Charge Waveform